Serial No. 09/653,295

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- deposited on the exposed portions of layers 52, 54, 56, 58 and 60 as well as the dielectric layer 70 and exposed regions of Cu in the metallization level 30.
- (9) Please replace the sentence at page 8, line 1 with the following rewritten sentence: A lower conductor level 30 includes a runner portion 123 effecting connection between lower plate 52 and a via portion 92 of level 40.
- (10) Please replace the sentence at page 8, line 8 with the following rewritten sentence: Connections to individual layers 122 are made through via portions 126 and conductive runners 120, 123 and 125 to configure four capacitors connected in parallel.

IN THE CLAIMS

1. (Amended) A monolithic integrated circuit comprising:

at least first and second levels of interconnect conductor for connection to a semiconductor layer; and

a stack of alternating conductive and insulative layers formed in vertical alignment with respect to an underlying plane and formed between the first and second levels of conductor, including

- a first conductive layer,
- a first insulator layer formed over the first conductive layer,
- a second conductive layer formed over the first insulative layer ,
- a second insulator layer formed over the second conductive layer, and
- a third conductive layer formed over the second insulative layer,

with the first and third conductive layers commonly connected.